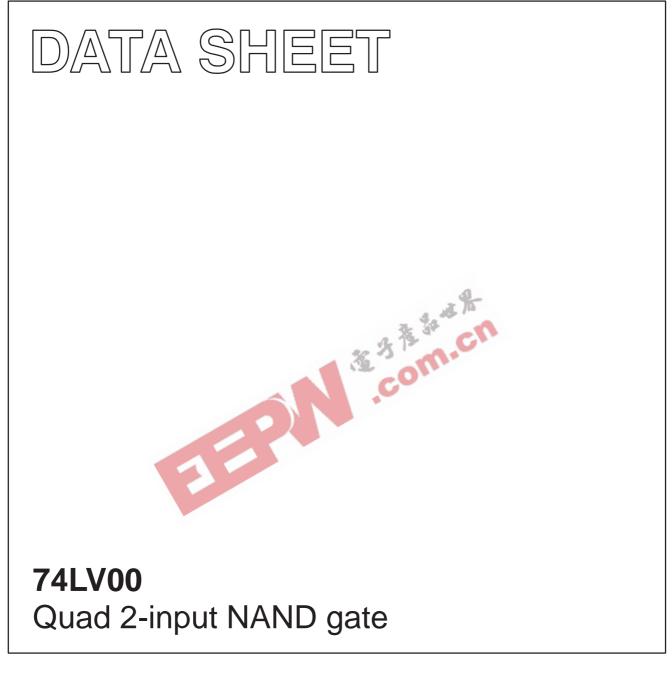
INTEGRATED CIRCUITS



Product specification Supersedes data of 1998 Apr 13 IC24 Data Handbook 1998 Apr 20



74LV00

FEATURES

- Wide operating voltage: 1.0 to 5.5 V
- Optimized for low voltage applications: 1.0 to 3.6 V
- Accepts TTL input levels between V_{CC} = 2.7 V and V_{CC} = 3.6 V
- Typical V_{OLP} (output ground bounce) < 0.8 V at V_{CC} = 3.3 V, $T_{amb} = 25^{\circ}C$
- Typical V_{OHV} (output V_{OH} undershoot) > 2 V at V_{CC} = 3.3 V, $T_{amb} = 25^{\circ}C$
- Output capability: standard
- I_{CC} category: SSI

QUICK REFERENCE DATA

GND = 0 V; $T_{amb} = 25^{\circ}C$; $t_r = t_f \le 2.5$ ns

DESCRIPTION

The 74LV00 is a low-voltage Si-gate CMOS device that is pin and function compatible with 74HC/HCT00.

The 74LV00 provides the 2-input NAND function.

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t _{PHL} /t _{PLH}	Propagation delay nA, nB to nY	$C_L = 15 \text{ pF};$ $V_{CC} = 3.3 \text{ V}$	7	ns
Cl	Input capacitance		3.5	pF
C _{PD}	Power dissipation capacitance per gate	See Notes 1 and 2	22	pF
$P_D = C_{PD} \times V_{CC}^2 \times$	nine the dynamic power dissipation (P _D in $f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where: In MHz; C _L = output load capacitance in pF;			

NOTES:

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μ W) P_D = C_{PD} × V_{CC}² × f_i + \sum (C_L × V_{CC}² × f_o) where: f_i = input frequency in MHz; C_L = output load capacitance in pF; f_o = output frequency in MHz; V_{CC} = supply voltage in V; \sum (C_L × V_{CC}² × f_o) = sum of the outputs.

2. The condition is $V_I = GND$ to V_{CC}

ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	PKG. DWG. #
14-Pin Plastic DIL	–40°C to +125°C	74LV00 N	74LV00 N	SOT27-1
14-Pin Plastic SO	–40°C to +125°C	74LV00 D	74LV00 D	SOT108-1
14-Pin Plastic SSOP Type II	–40°C to +125°C	74LV00 DB	74LV00 DB	SOT337-1
14-Pin Plastic TSSOP Type I	-40°C to +125°C	74LV00 PW	74LV00PW DH	SOT402-1

PIN DESCRIPTION

PIN NUMBER	SYMBOL	FUNCTION
1, 4, 9, 12	1A – 4A	Data inputs
2, 5, 10, 13	1B – 4B	Data inputs
3, 6, 8, 11	1Y – 4Y	Data outputs
7	GND	Ground (0 V)
14	V _{CC}	Positive supply voltage

FUNCTION TABLE

INP	INPUTS					
nA	nA nB					
L	L	Н				
L	Н	Н				
н	L	Н				
н	н	L				

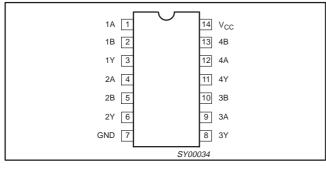
NOTES:

H = HIGH voltage level

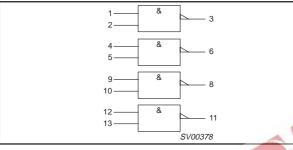
L = LOW voltage level

74LV00

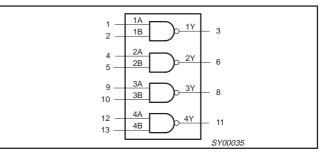
PIN CONFIGURATION



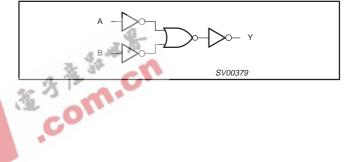
LOGIC SYMBOL (IEEE/IEC)



LOGIC SYMBOL



LOGIC DIAGRAM (ONE GATE)



RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CC}	DC supply voltage	See Note 1	1.0	3.3	5.5	V
VI	Input voltage		0	-	V _{CC}	V
V _O	Output voltage		0	-	V _{CC}	V
T _{amb}	Operating ambient temperature range in free air	See DC and AC characteristics	-40 -40		+85 +125	°C
t _r , t _f	Input rise and fall times	$V_{CC} = 1.0V \text{ to } 2.0V \\ V_{CC} = 2.0V \text{ to } 2.7V \\ V_{CC} = 2.7V \text{ to } 3.6V \\ V_{CC} = 3.6V \text{ to } 5.5V$	- - -	- - - -	500 200 100 50	ns/V

NOTE: 1. The LV is guaranteed to function down to $V_{CC} = 1.0V$ (input levels GND or V_{CC}); DC characteristics are guaranteed from $V_{CC} = 1.2V$ to $V_{CC} = 5.5V$.

74LV00

ABSOLUTE MAXIMUM RATINGS^{1, 2}

In accordance with the Absolute Maximum Rating System (IEC 134).

Voltages are referenced to GND (ground = 0V).

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage		-0.5 to +7.0	V
±I _{IK}	DC input diode current	$V_{I} < -0.5 \text{ or } V_{I} > V_{CC} + 0.5 V$	20	mA
±Ι _{ΟΚ}	DC output diode current	$V_{\rm O}$ < -0.5 or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5V	50	mA
±IO	DC output source or sink current – standard outputs	$-0.5V < V_{O} < V_{CC} + 0.5V$	25	mA
±I _{GND} , ±I _{CC}	DC V _{CC} or GND current for types with – standard outputs		50	mA
T _{stg}	Storage temperature range		-65 to +150	°C
P _{TOT}	Power dissipation per package – plastic DIL – plastic mini-pack (SO) – plastic shrink mini-pack (SSOP and TSSOP)	for temperature range: -40 to +125°C above +70°C derate linearly with 12 mW/K above +70°C derate linearly with 8 mW/K above +60°C derate linearly with 5.5 mW/K	750 500 400	mW

NOTES:
Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

DC ELECTRICAL CHARACTERISTICS

Over recommended operating conditions. Voltages are referenced to GND (ground = 0V).

					LIMITS			
SYMBOL	PARAMETER	TEST CONDITIONS	-40	°C to +8	5°C	-40°C to	o +125°C	
			MIN	TYP ¹	MAX	MIN	MAX	1
		$V_{CC} = 1.2V$	0.9			0.9		
V	HIGH level Input	$V_{CC} = 2.0V$	1.4			1.4		
V_{IH}	voltage	$V_{CC} = 2.7$ to 3.6V	2.0			2.0		1 `
		V _{CC} = 4.5 to 5.5V	0.7*V _{CC}			0.7*V _{CC}		1
		V _{CC} = 1.2V			0.3		0.3	
VIL	LOW level Input	$V_{CC} = 2.0V$			0.6		0.6	
۷IL	voltage	V _{CC} = 2.7 to 3.6V			0.8		0.8	1 `
	V _{CC} = 4.5 to 5.5			0.3*V _{CC}		0.3*V _{CC}	1	
		$V_{CC} = 1.2V; V_I = V_{IH} \text{ or } V_{IL;} - I_O = 100 \mu A$		1.2				
V _{OH} HIGH level output voltage; all outputs	$V_{CC} = 2.0V; V_I = V_{IH} \text{ or } V_{IL;} - I_O = 100 \mu A$	1.8	2.0		1.8		1	
	$V_{CC} = 2.7V; V_I = V_{IH} \text{ or } V_{IL;} - I_O = 100 \mu A$	2.5	2.7		2.5		V	
		$V_{CC} = 3.0V; V_I = V_{IH} \text{ or } V_{IL;} - I_O = 100 \mu A$	2.8	3.0		2.8]
		$V_{CC} = 4.5V; V_I = V_{IH} \text{ or } V_{IL;} - I_O = 100 \mu A$	4.3	4.5		4.3		1
V _{OH}	HIGH level output voltage;	V_{CC} = 3.0V; V_I = V_{IH} or V_{IL} ; $-I_O$ = 6mA	2.40	2.82		2.20		v
♥ OH	STANDARD outputs	V_{CC} = 4.5V; V_I = V_{IH} or V_{IL} , $-I_O$ = 12mA	3.60	4.20		3.50		
		V_{CC} = 1.2V; V_{I} = V_{IH} or V_{IL} ; I_{O} = 100 μ A		0				
		V_{CC} = 2.0V; V_I = V_{IH} or $V_{IL;} I_O$ = 100 μ A		0	0.2		0.2]
V _{OL}	LOW level output voltage; all outputs	V_{CC} = 2.7V; V_I = V_{IH} or V_{IL} ; I_O = 100 μ A		0	0.2		0.2	V
vonago, an outputo	$V_{CC} = 3.0V$; $V_I = V_{IH}$ or V_{IL} ; $I_O = 100\mu A$		0	0.2		0.2]	
		V_{CC} = 4.5V; V_I = V_{IH} or V_{IL} ; I_O = 100 μ A		0	0.2		0.2	
V _{OL}	LOW level output voltage;	V_{CC} = 3.0V; V_{I} = V_{IH} or V_{IL} ; I_{O} = 6mA		0.25	0.40		0.50	v
V OL	STANDARD outputs	V_{CC} = 4.5V; V_{I} = V_{IH} or $V_{IL;}$ I_{O} = 12mA		0.35	0.55		0.65	

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DC ELECTRICAL CHARACTERISTICS (Continued)

Over recommended operating conditions. Voltages are referenced to GND (ground = 0V).

			LIMITS						
SYMBOL	PARAMETER	TEST CONDITIONS	-40	°C to +85	S°C	-40°C to	UNIT		
			MIN	TYP ¹	MAX	MIN	MAX		
lı	Input leakage current	V_{CC} = 5.5V; V_{I} = V_{CC} or GND			1.0		1.0	μΑ	
I _{CC}	Quiescent supply current; SSI	$V_{CC} = 5.5V; V_I = V_{CC} \text{ or GND}; I_O = 0$			20.0		40	μA	
ΔI _{CC}	Additional quiescent supply current	$V_{CC} = 2.7V$ to 3.6V; $V_{I} = V_{CC} - 0.6V$			500		850	μΑ	

NOTE:

1. All typical values are measured at T_{amb} = 25°C.

AC CHARACTERISTICS

GND = 0V; $t_r = t_f \le 2.5$ ns; $C_1 = 50$ pF; $R_1 = 1$ K Ω

			CONDITION		MITS	
SYMBOL PARAMETER		WAVEFORM	CONDITION	–40 to +85 °C	–40 to +125 °C	UNIT
		V _{CC} (V)	MIN TYP1	MAX MIN MAX		
			1.2	45		
	Descent for dataset		2.0	15	26 31	
t _{PHL/PLH}	Propagation delay nA, nB to nY	Figures 1, 2	2.7	11	18 23	ns
			3.0 to 3.6	9 ²	15 18	
			4.5 to 5.5	6.5 ³	11 14	

NOTES:

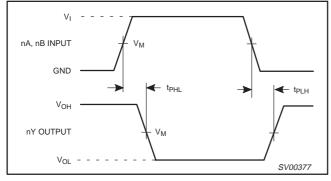
1. Unless otherwise stated, all typical values are measured at $T_{amb} = 25^{\circ}C$. 2. Typical values are measured at $V_{CC} = 3.3 \text{ V}$. 3. Typical values are measured at $V_{CC} = 5.0 \text{ V}$.

AC WAVEFORMS

 V_M = 1.5 V at $V_{CC} \geq 2.7$ V and ≤ 3.6 V;

 $V_{M} = 0.5 \times V_{CC}$ at $V_{CC} < 2.7$ V and ≥ 4.5 V;

 V_{OL} and V_{OH} are the typical output voltage drop that occur with the output load.





TEST CIRCUIT

1

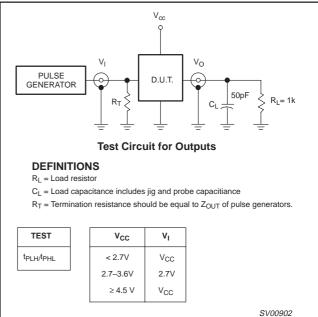
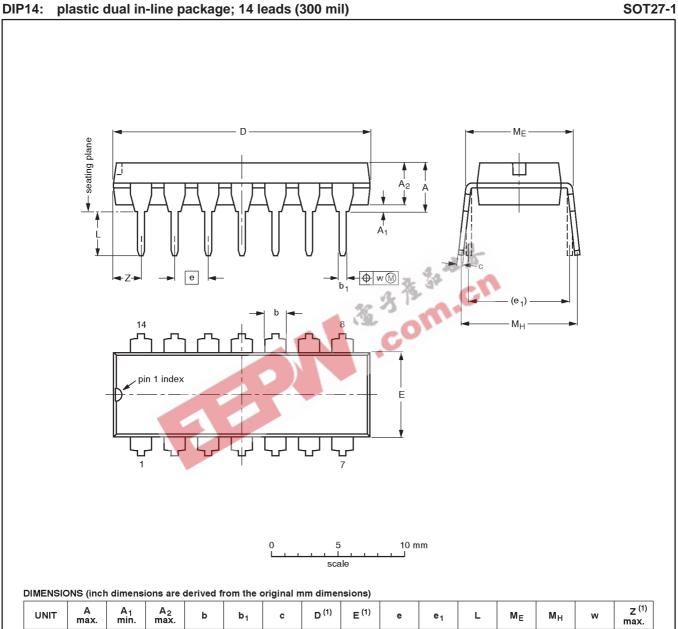


Figure 2. Load circuitry for switching times.

74LV00

2.2

0.087



UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	c	D ⁽¹⁾	E ⁽¹⁾	e	e ₁	L	ME	M _H	w
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254
inches	0.17	0.020	0.13	0.068	0.021	0.014	0.77	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39	0.01

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFEF	RENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC EIAJ		PROJECTION	1550E DATE	
SOT27-1	050G04	MO-001AA			-92-11-17 95-03-11	

74LV00

SOT108-1 plastic small outline package; 14 leads; body width 3.9 mm SO14: Α Х = v 🕅 A He Q (A_3) pin 1 index Ŧ ⊕ w (M) detail X 2.5 5 m m scale DIMENSIONS (inch dimensions are derived from the original mm dimensions) Α D⁽¹⁾ E⁽¹⁾ Z⁽¹⁾ UNIT Q A₁ A₂ с е ${\sf H}_{\sf E}$ L v w θ A_3 bp Lp у max. 0.25 1.45 0.49 0.25 8.75 4.0 6.2 1.0 0.7 0.7 mm 1.75 0.25 1.27 1.05 0.25 0.25 0.1 1.25 8.55 5.8 0.6 0.3 0.10 0.36 0.19 3.8 0.4 8°

Note

inches

0.0098

0.0039

0.069

0.057

0.049

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

0.01

0.019

0.014

0.0098

0.0075

0.35

0.34

0.16

0.15

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE	
SOT108-1	076E06S	MS-012AB			91-08-13 95-01-23	

0.050

0.24

0.23

0.041

0.039

0.016

0.028

0.024

0.01

0.01

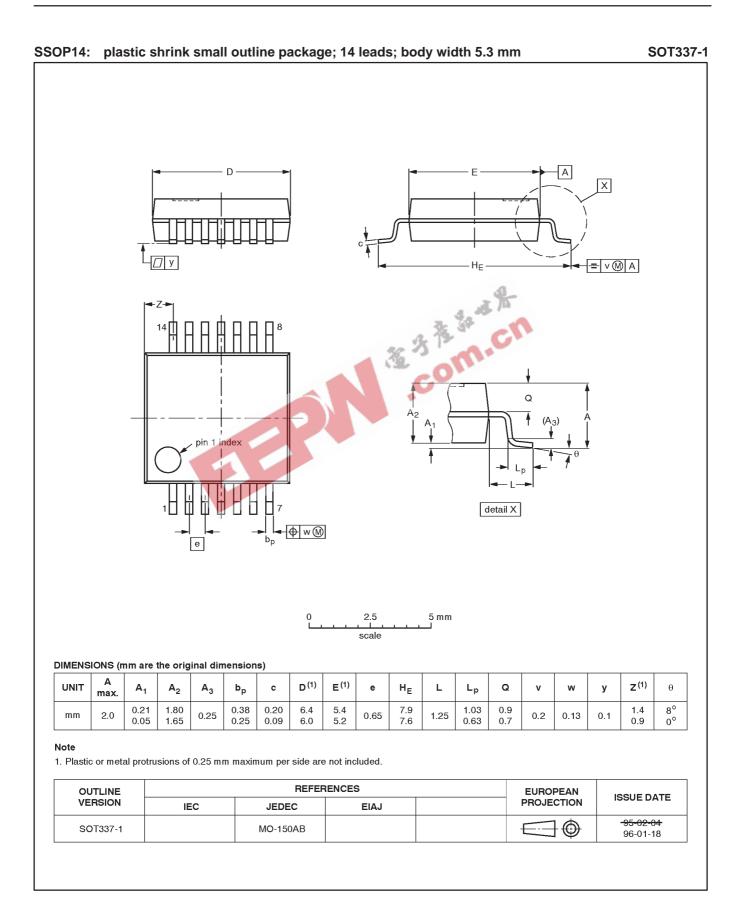
0.004

0°

0.028

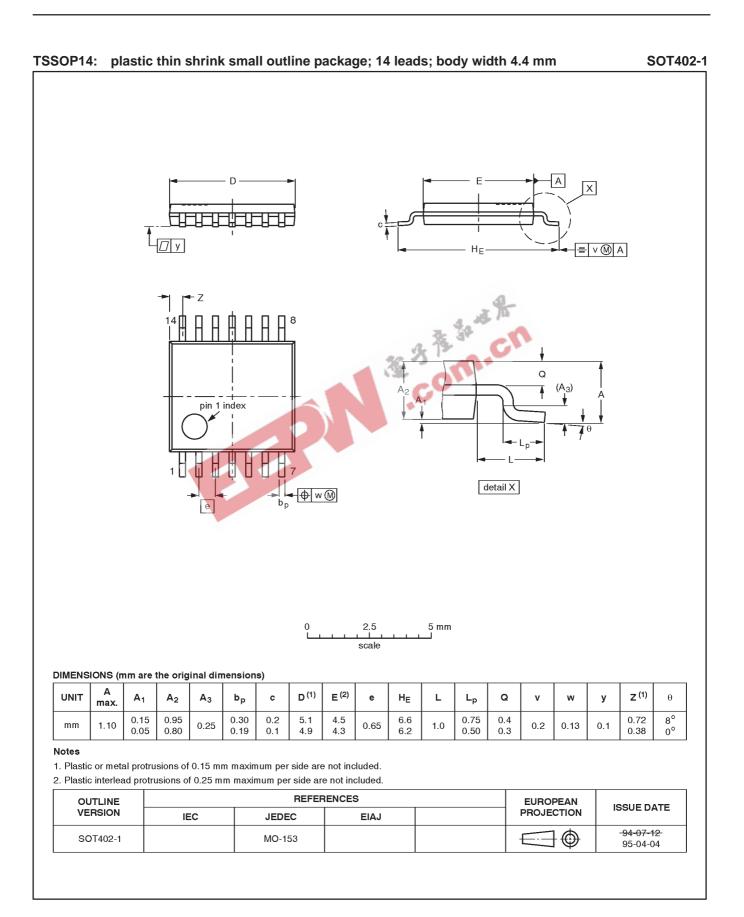
0.012

74LV00



1998 Apr 20

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74LV00

DEFINITIONS		
Data Sheet Identification	Product Status	Definition
Objective Specification	Formative or in Design	This data sheet contains the design target or goal specifications for product development. Specifications may change in any manner without notice.
Preliminary Specification	Preproduction Product	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
Product Specification	Full Production	This data sheet contains Final Specifications. Philips Semiconductors reserves the right to make changes at any time without notice, in order to improve design and supply the best possible product.

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